

# IRF7910PbF

HEXFET® Power MOSFET

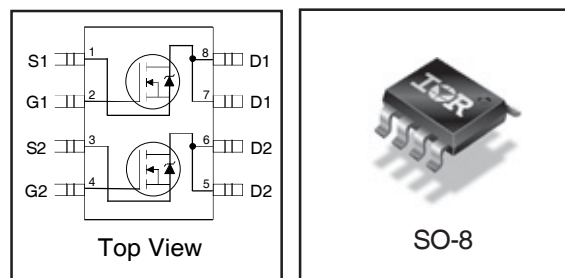
## Applications

- High Frequency 3.3V and 5V input Point-of-Load Synchronous Buck Converters for Netcom and Computing Applications
- Power Management for Netcom, Computing and Portable Applications
- Lead-Free

## Benefits

- Ultra-Low Gate Impedance
- Very Low  $R_{DS(on)}$
- Fully Characterized Avalanche Voltage and Current

$V_{DSS}$	$R_{DS(on)}$ max	$I_D$
12V	15m $\Omega$ @ $V_{GS} = 4.5V$	10A



## Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
$V_{DS}$	Drain-Source Voltage	12	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	10	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	7.9	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	79	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation <sup>④</sup>	2.0	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation <sup>④</sup>	1.3	W
	Linear Derating Factor	16	mW/ $^\circ C$
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

## Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	42	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient <sup>④</sup>	—	62.5	

Notes <sup>①</sup> through <sup>④</sup> are on page 8  
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## Static @ T<sub>J</sub> = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	12	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.01	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	11.5	15	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 8.0A ③
		—	20	50		V <sub>GS</sub> = 2.8V, I <sub>D</sub> = 5.0A
V <sub>GS(th)</sub>	Gate Threshold Voltage	0.6	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	100	μA	V <sub>DS</sub> = 9.6V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 9.6V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	200	nA	V <sub>GS</sub> = 12V
	Gate-to-Source Reverse Leakage	—	—	-200		V <sub>GS</sub> = -12V

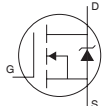
## Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)

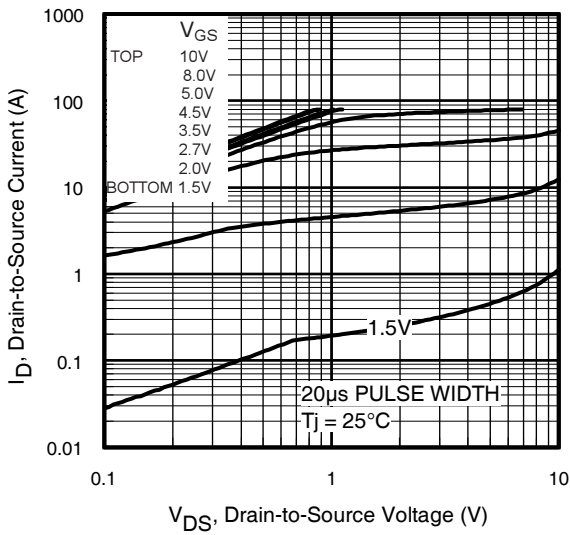
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g <sub>fs</sub>	Forward Transconductance	18	—	—	S	V <sub>DS</sub> = 6.0V, I <sub>D</sub> = 8.0A
Q <sub>g</sub>	Total Gate Charge	—	17	26	nC	I <sub>D</sub> = 8.0A
Q <sub>gs</sub>	Gate-to-Source Charge	—	4.4	—		V <sub>DS</sub> = 6.0V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	5.2	—		V <sub>GS</sub> = 4.5V
Q <sub>oss</sub>	Output Gate Charge	—	16	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 10V
t <sub>d(on)</sub>	Turn-On Delay Time	—	9.4	—	ns	V <sub>DD</sub> = 6.0V
t <sub>r</sub>	Rise Time	—	22	—		I <sub>D</sub> = 8.0A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	16	—		R <sub>G</sub> = 1.8Ω
t <sub>f</sub>	Fall Time	—	6.3	—		V <sub>GS</sub> = 4.5V ③
C <sub>iss</sub>	Input Capacitance	—	1730	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	1340	—		V <sub>DS</sub> = 6.0V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	330	—		f = 1.0MHz

## Avalanche Characteristics

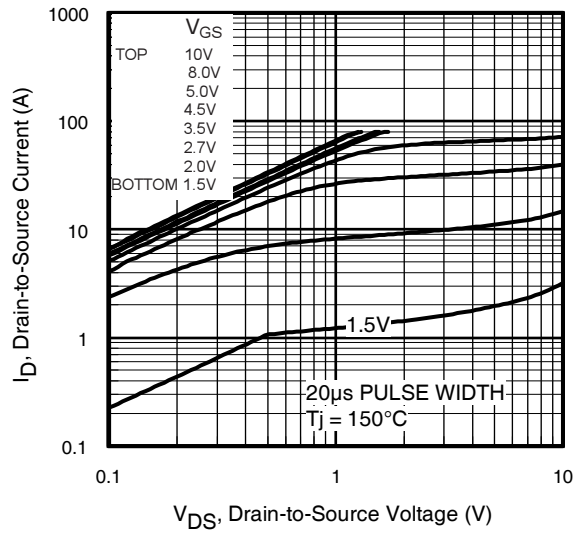
Symbol	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy②	—	100	mJ
I <sub>AR</sub>	Avalanche Current①	—	8.0	A

## Diode Characteristics

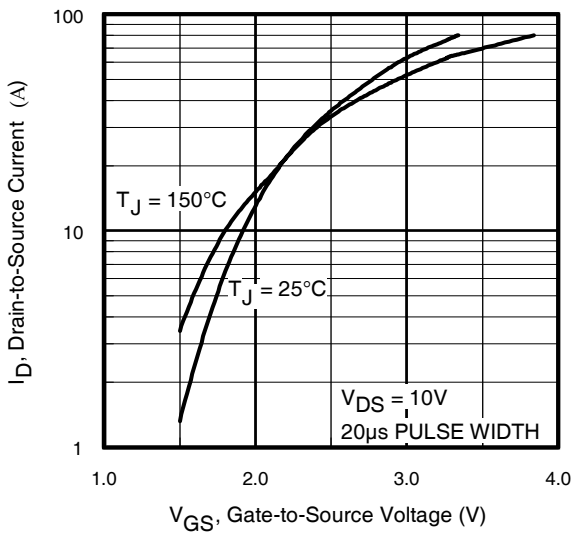
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	1.8	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	79		
V <sub>SD</sub>	Diode Forward Voltage	—	0.85	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 8.0A, V <sub>GS</sub> = 0V ③
		—	0.70	—		T <sub>J</sub> = 125°C, I <sub>S</sub> = 8.0A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	50	75	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 8.0A, V <sub>R</sub> = 12V
Q <sub>rr</sub>	Reverse Recovery Charge	—	60	90	nC	di/dt = 100A/μs ③
t <sub>rr</sub>	Reverse Recovery Time	—	51	77	ns	T <sub>J</sub> = 125°C, I <sub>F</sub> = 8.0A, V <sub>R</sub> = 12V
Q <sub>rr</sub>	Reverse Recovery Charge	—	60	90	nC	di/dt = 100A/μs ③



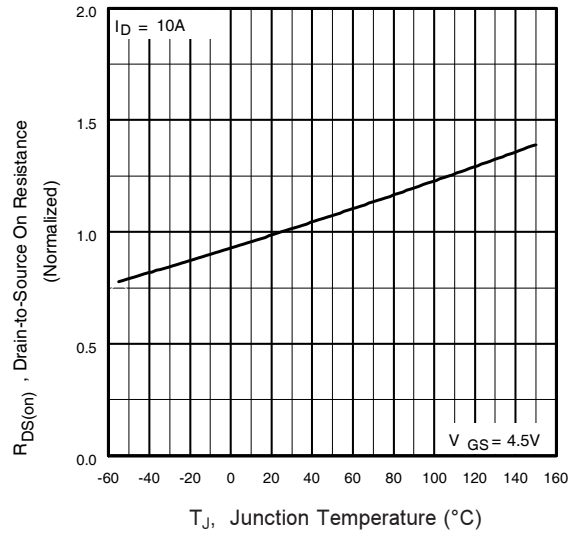
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

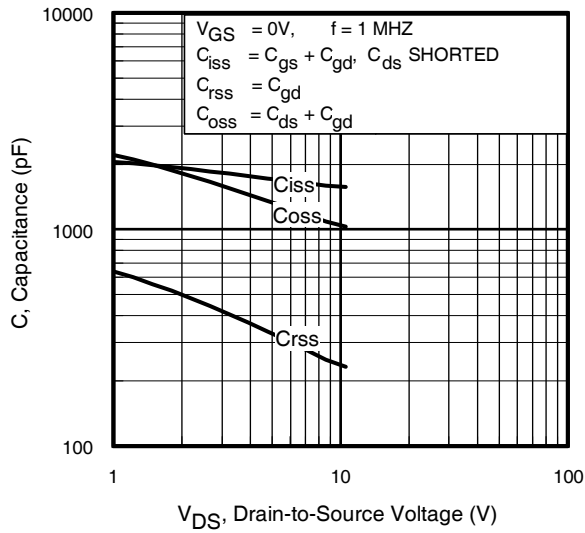


**Fig 3.** Typical Transfer Characteristics

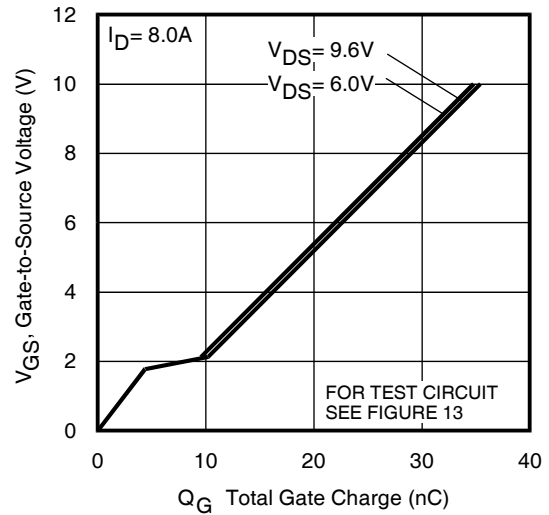


**Fig 4.** Normalized On-Resistance Vs. Temperature

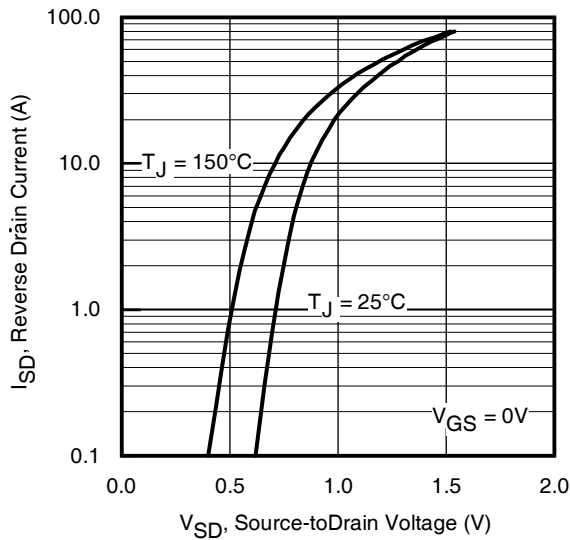
# IRF7910PbF



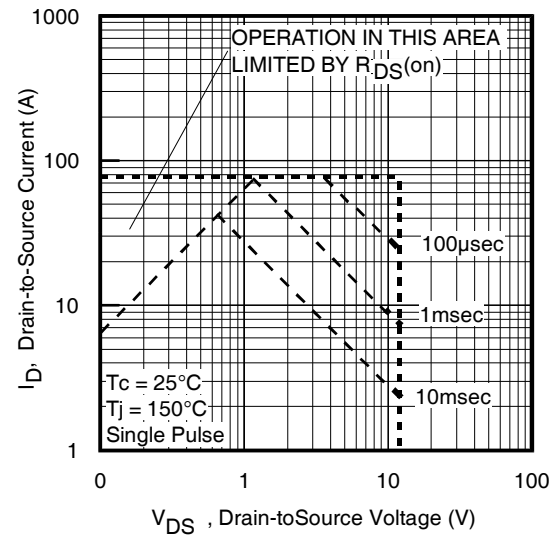
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



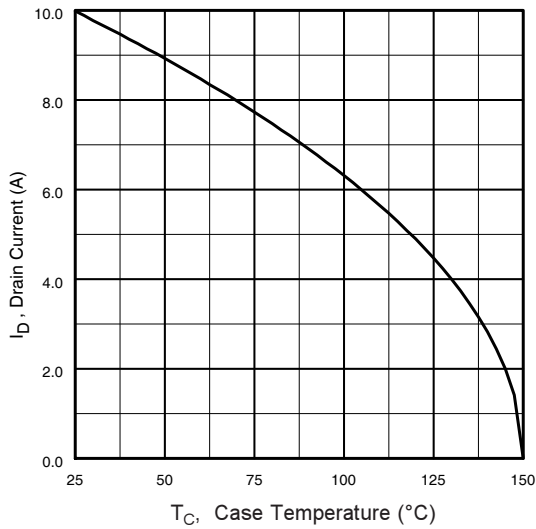
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



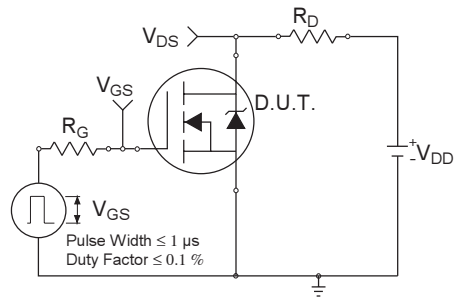
**Fig 7.** Typical Source-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area



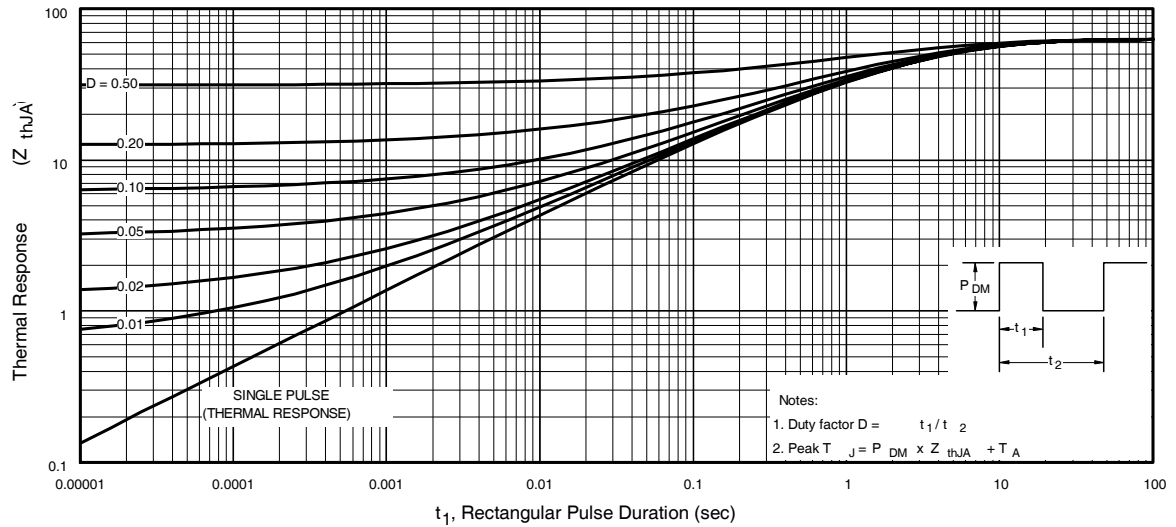
**Fig 9.** Maximum Drain Current Vs. Ambient Temperature



**Fig 10a.** Switching Time Test Circuit



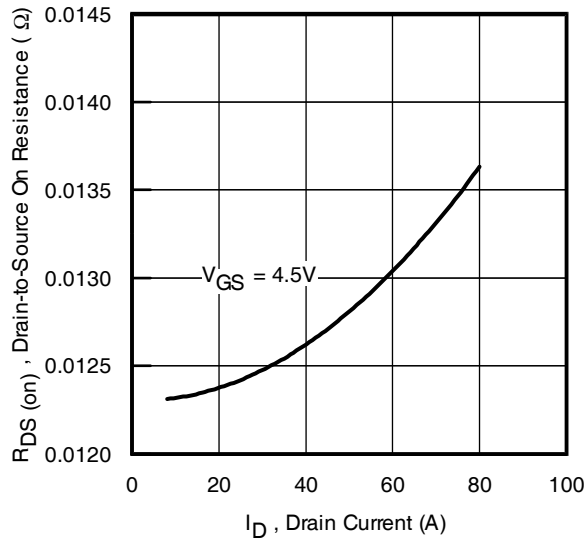
**Fig 10b.** Switching Time Waveforms



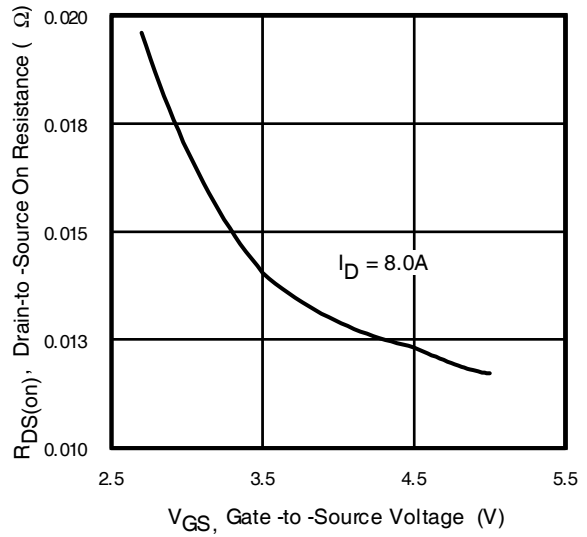
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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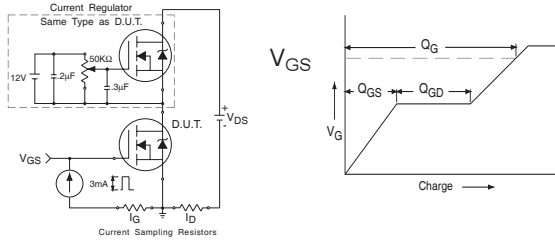
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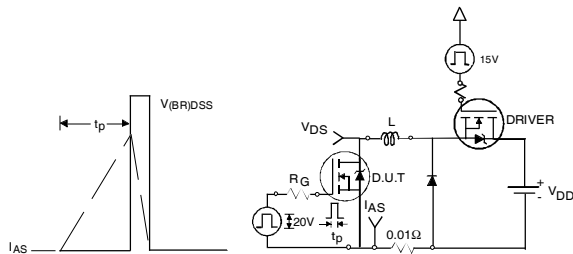
**Fig 12.** On-Resistance Vs. Drain Current



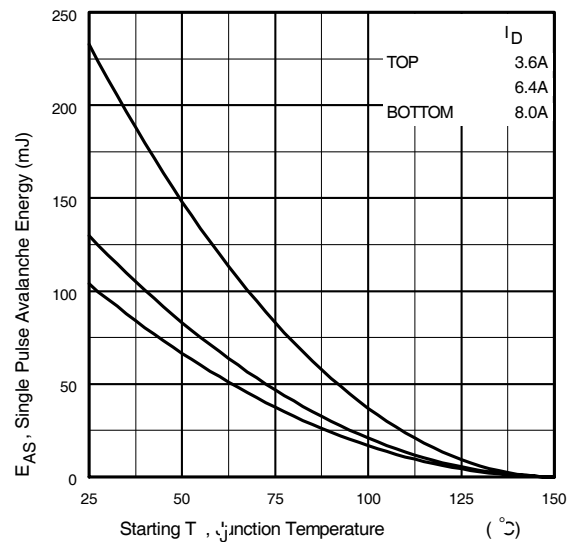
**Fig 13.** On-Resistance Vs. Gate Voltage



**Fig 14a&b.** Basic Gate Charge Test Circuit and Waveform



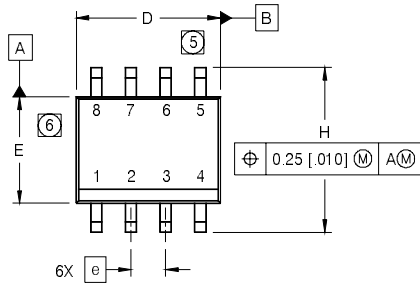
**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms



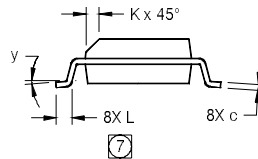
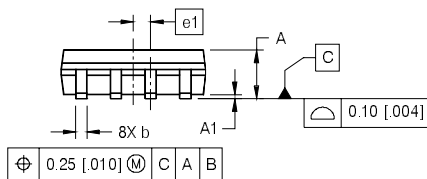
**Fig 15c.** Maximum Avalanche Energy Vs. Drain Current

## SO-8 Package Outline (MOSFET & Fetky)

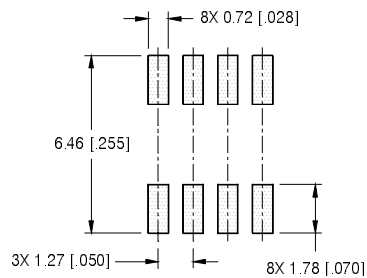
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



### FOOTPRINT

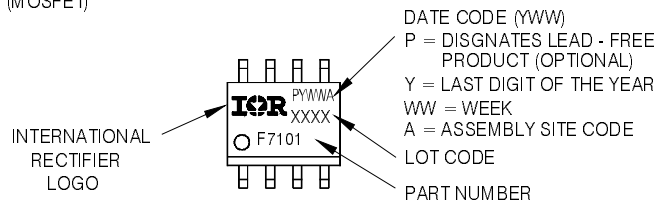


### NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

## SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



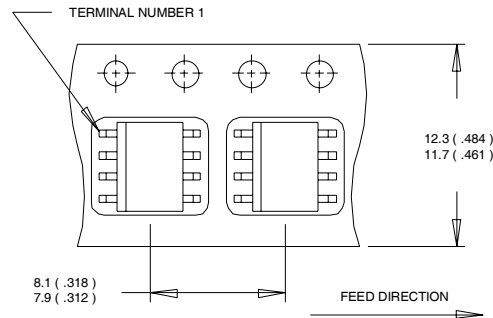
Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>  
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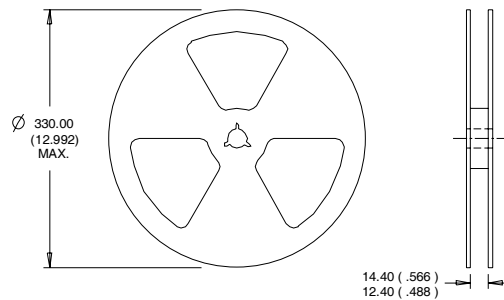
## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)

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- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

**Note:** For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 3.2\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 8.0\text{A}$ .
- ③ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ When mounted on 1 inch square copper board,  $t < 10$  sec

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualifications Standards can be found on IR's Web site.

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**IR WORLD HEADQUARTERS:** 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105  
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